

MEMORY CELL STRINGS IN A RESISTIVE CROSS POINT MEMORY CELL ARRAY

Abstract of the Disclosure

A data storage device that includes a memory cell string. The memory cell string includes a first memory cell and a second memory cell. The device also includes a circuit coupled to a node between the first memory cell and a second memory cell. The circuit is configured to detect a voltage change at the node in response to a voltage being provided to the memory cell string and the first memory cell being written to a first state.